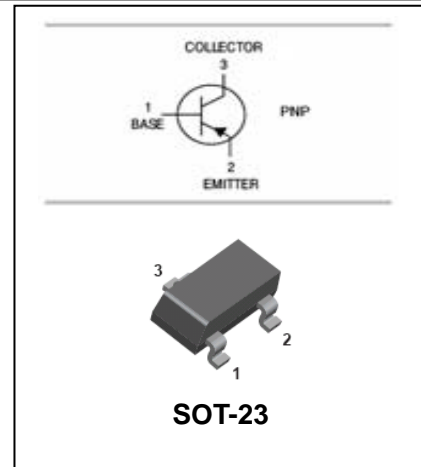


## Silicon Epitaxial Planar Transistor

## 2SA1036

### FEATURES

- Large  $I_{C,ICMAX.} = -500\text{mA}$ .
- Low  $V_{CE(sat)}$ . Ideal for low-voltage operation.
- Complements the 2SC2411.



### APPLICATIONS

- Ideal for low-voltage operation.

### ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1036□	HP/HQ/HR	SOT-23

- : none is for Lead Free package;  
“G” is for Halogen Free package.

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-32	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-500	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

# Silicon Epitaxial Planar Transistor

# 2SA1036

## ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -3V, I_C = -10mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.4	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -20mA$ $f = 100MHz$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		7		pF

## CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390

## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

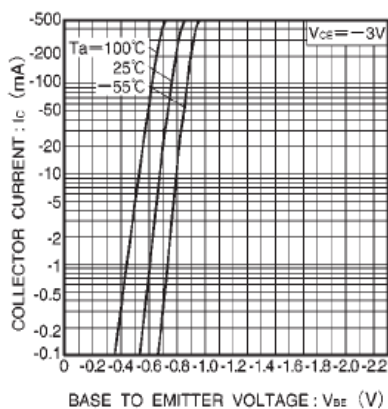


Fig.1 Grounded emitter propagation

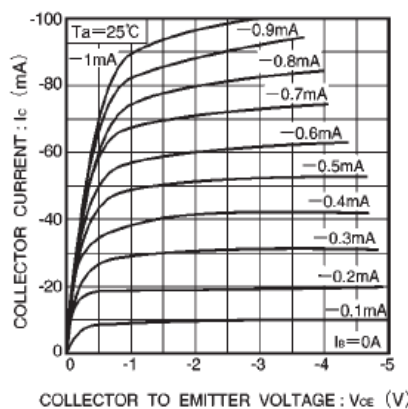


Fig.2 Grounded emitter output characteristics (I)

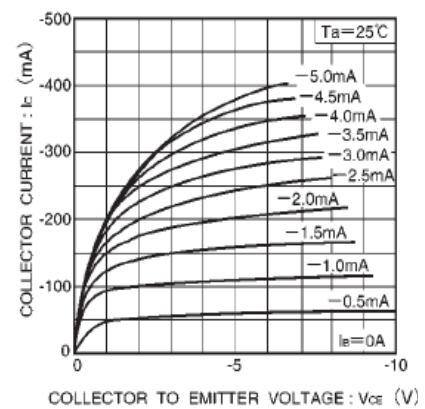


Fig.3 Grounded emitter output characteristics (II)

Silicon Epitaxial Planar Transistor

2SA1036

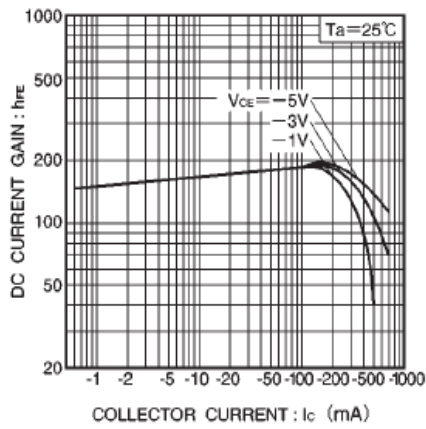


Fig.4 DC current gain vs. collector current ( I )

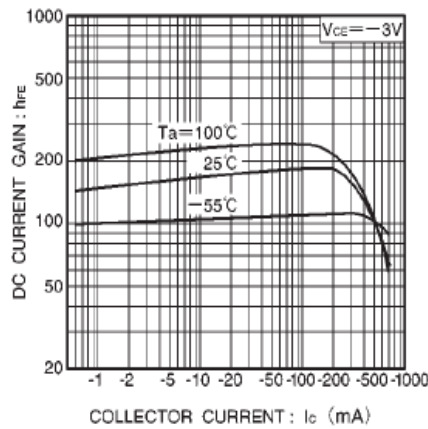


Fig.5 DC current gain vs. collector current ( II )

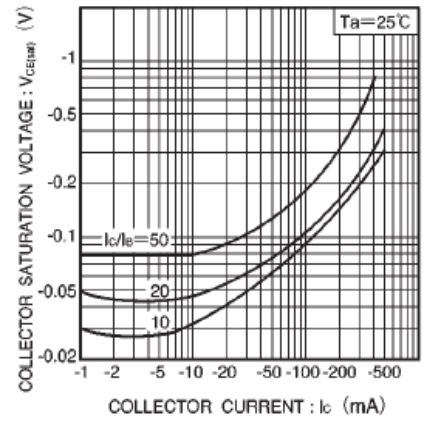


Fig.6 Collector-emitter saturation voltage vs. collector current ( I )

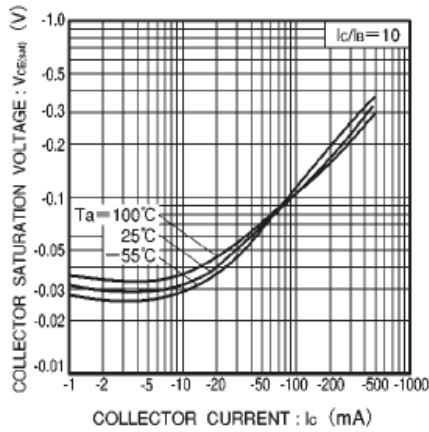


Fig.7 Collector-emitter saturation voltage vs. collector current ( II )

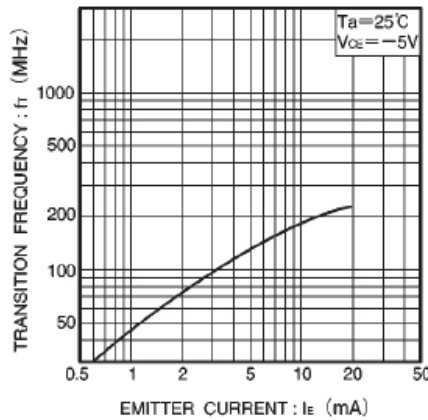


Fig.8 Gain bandwidth product vs. emitter current

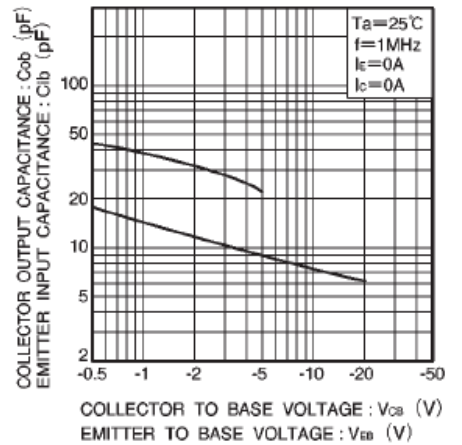


Fig.9 Collector output capacitance vs. collector-base voltage. Emitter input capacitance vs. emitter-base voltage

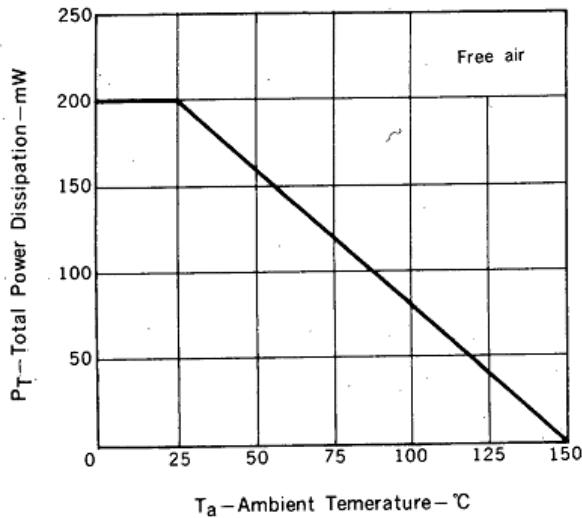


Fig.10 TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

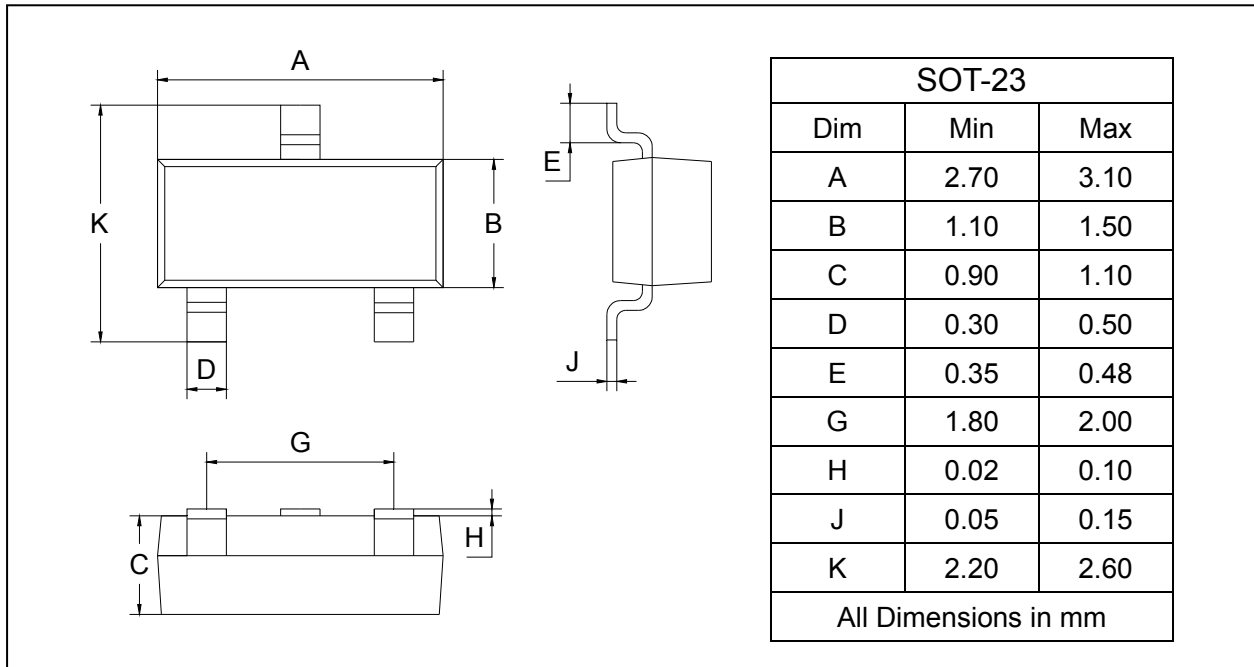
## Silicon Epitaxial Planar Transistor

## 2SA1036

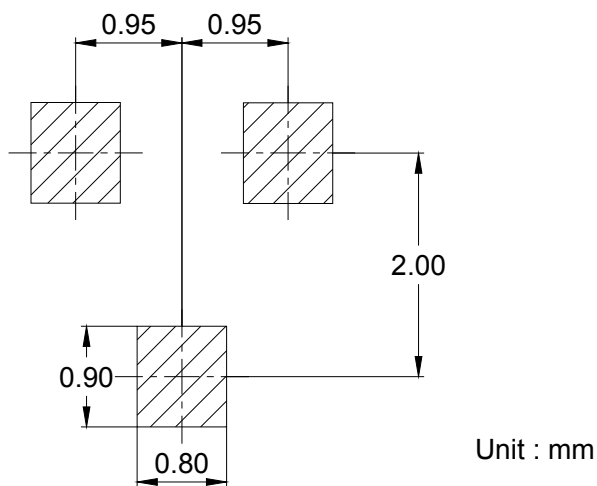
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
2SA1036	SOT-23	3000/Tape&Reel